INCREASING THE ETCH RESISTANCE OF PHOTORESISTS

Abstract of the Disclosure

Materials may be utilized as photoresists which have relatively plasma poor etch resistance. Examples include acrylates and fluorinated polymers, which have very good transparency but poor etch resistance. Materials with relatively poor etch resistance may be first applied to the semiconductor wafer and patterned. After they have been patterned, their etch resistance may be improved. For example, the etch resistance may be improved by applying an absorbate which may be cross-linked or polymerized to increase the etch resistance of the already patterned material. Thereafter, the material with the improved etch resistance may be used as an etching mask.